Docket:: TSMC 00 - 355

S/N: 09/765,044

In the Claims

Please add the following claims 29 to 31:

29. The method of claim 1, wherein the porous silicon oxide film is thermally deposited without plasma power.



- 30. The method of claim 11, wherein the porous silicon oxide film is thermally deposited without plasma power.
- 31. The method of claim 20, wherein the porous silicon oxide film is thermally deposited without plasma power.

Remarks

Examiner Brewster is thanked for the thorough Office Action.

Claim Rejections

The Rejection Of Claims 1, 2, 8 To 11, 17 To 20 And 26 To 28 Under 35 U.S.C. §103(a) as Being Unpatentable Over Morozumi et al. (U.S. Patent No. 6,194,304) In View Of Ngo (U.S. Patent No. 6,054,735)